NSS12201LT1G

12 V, 4.0 A, Low V$_{CE(sat)}$ NPN Transistor

ON Semiconductor's e^{2}PowerEdge family of low V$_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage (V$_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC−DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e^{2}PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V$_{CEO}$	12	Vdc
Collector-Base Voltage	V$_{CBO}$	12	Vdc
Emitter-Base Voltage	V$_{EBO}$	6.0	Vdc
Collector Current – Continuous	I$_C$	2.0	A
Collector Current – Peak	I$_{CM}$	4.0	A
Electrostatic Discharge	ESD	HBM Class 3B MM Class C	

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T_A = 25°C	P$_D$ (Note 1)	460	mW
Derate above 25°C		3.7	mW/°C
Thermal Resistance, Junction−to−Ambient	R$_{\theta JA}$ (Note 1)	270	°C/W
Total Device Dissipation T_A = 25°C	P$_D$ (Note 2)	540	mW
Derate above 25°C		4.3	mW/°C
Thermal Resistance, Junction−to−Ambient	R$_{\theta JA}$ (Note 2)	230	°C/W
Junction and Storage Temperature Range	T$_J$, T$_{stg}$	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
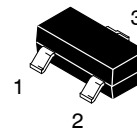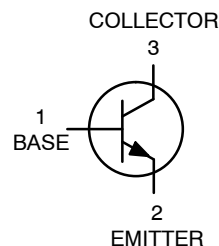1. FR−4 @ 100 mm^2, 1 oz. copper traces.
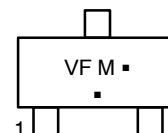2. FR−4 @ 500 mm^2, 1 oz. copper traces.

1

ON Semiconductor®

12 VOLTS, 4.0 AMPS NPN LOW V$_{CE(sat)}$ TRANSISTOR EQUIVALENT R$_{DS(on)}$ 35 mΩ

COLLECTOR
3

1
BASE

2
EMITTER

SOT−23 (TO−236)
CASE 318
STYLE 6

MARKING DIAGRAM

VF M ▪

1

VF = Specific Device Code
M = Date Code*
▪ = Pb−Free Package
(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NSS12201LT1G	SOT−23 (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	12	–	–	Vdc
Collector – Base Breakdown Voltage (I_C = 0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	12	–	–	Vdc
Emitter – Base Breakdown Voltage (I_E = 0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	–	–	Vdc
Collector Cutoff Current (V_{CB} = 12 Vdc, I_E = 0)	I_{CBO}	–	–	0.1	µAdc
Emitter Cutoff Current (V_{EB} = 6.0 Vdc)	I_{EBO}	–	–	0.1	µAdc
ON CHARACTERISTICS					
DC Current Gain (Note 3) (I_C = 10 mA, V_{CE} = 2.0 V) (I_C = 500 mA, V_{CE} = 2.0 V) (I_C = 1.0 A, V_{CE} = 2.0 V) (I_C = 2.0 A, V_{CE} = 2.0 V)	h_{FE}	200 200 200 200	– 330 – –	– – – –	
Collector – Emitter Saturation Voltage (Note 3) (I_C = 0.1 A, I_B = 0.01 A) (I_C = 1.0 A, I_B = 0.100 A) (I_C = 1.0 A, I_B = 0.010 A) (I_C = 2.0 A, I_B = 0.2 A)	$V_{CE(sat)}$	– – – –	0.003 0.035 0.053 0.068	0.008 0.050 0.080 0.090	V
Base – Emitter Saturation Voltage (Note 3) (I_C = 1.0 A, I_B = 10 mA)	$V_{BE(sat)}$	–	0.760	0.900	V
Base – Emitter Turn–on Voltage (Note 3) (I_C = 1.0 A, V_{CE} = 2.0 V)	$V_{BE(on)}$	–	0.750	0.900	V
Cutoff Frequency (I_C = 100 mA, V_{CE} = 5.0 V, f = 100 MHz)	f_T	150	–	–	MHz
Input Capacitance (V_{EB} = 0.5 V, f = 1.0 MHz)	Cibo	–	–	450	pF
Output Capacitance (V_{CB} = 3.0 V, f = 1.0 MHz)	Cobo	–	–	75	pF
SWITCHING CHARACTERISTICS					
Delay (V_{CC} = 10 V, I_C = 750 mA, I_{B1} = 15 mA)	t_d	–	–	100	ns
Rise (V_{CC} = 10 V, I_C = 750 mA, I_{B1} = 15 mA)	t_r	–	–	100	ns
Storage (V_{CC} = 10 V, I_C = 750 mA, I_{B1} = 15 mA)	t_s	–	–	350	ns
Fall (V_{CC} = 10 V, I_C = 750 mA, I_{B1} = 15 mA)	t_f	–	–	110	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
3. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.
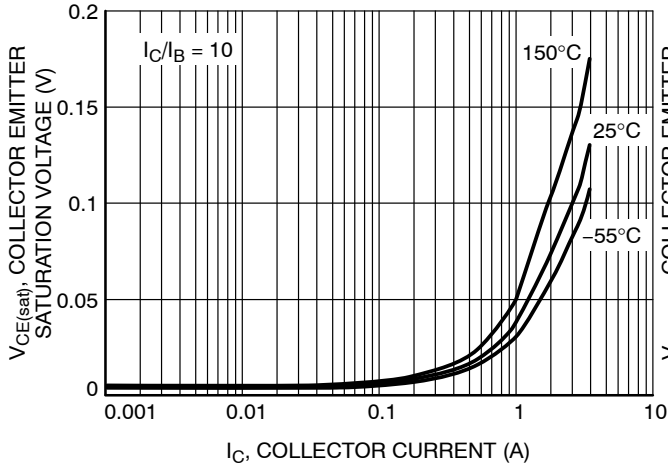
TYPICAL CHARACTERISTICS

Figure 1. Collector Emitter Saturation Voltage vs. Collector Current
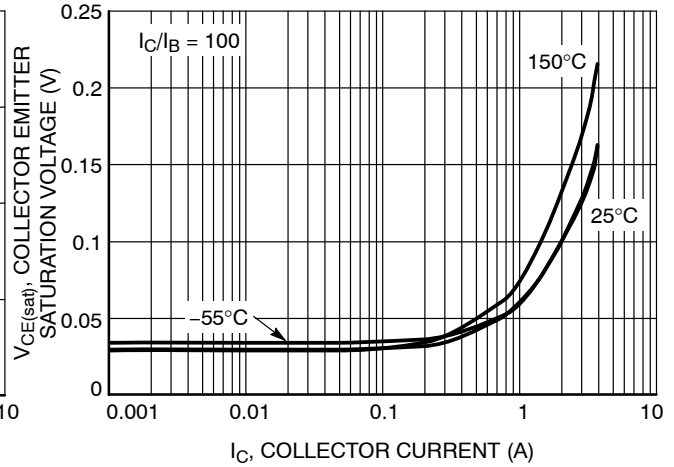

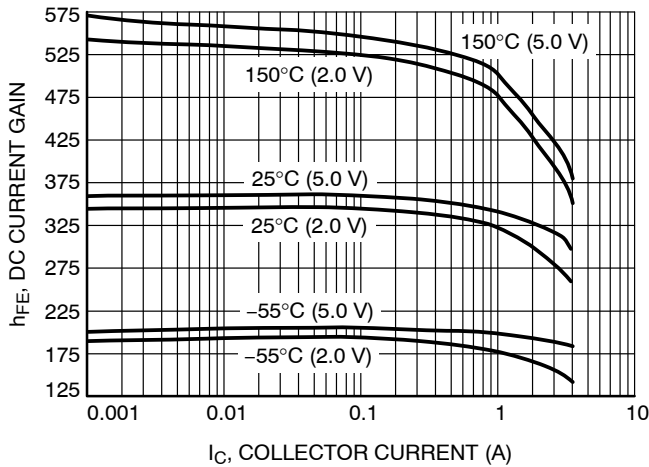Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

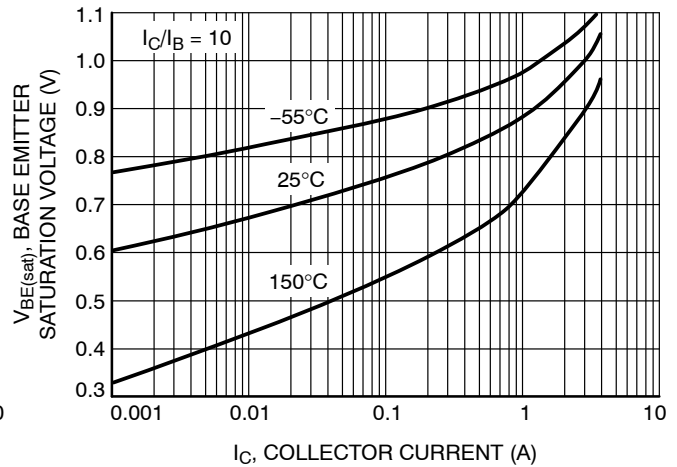Figure 3. DC Current Gain vs. Collector Current

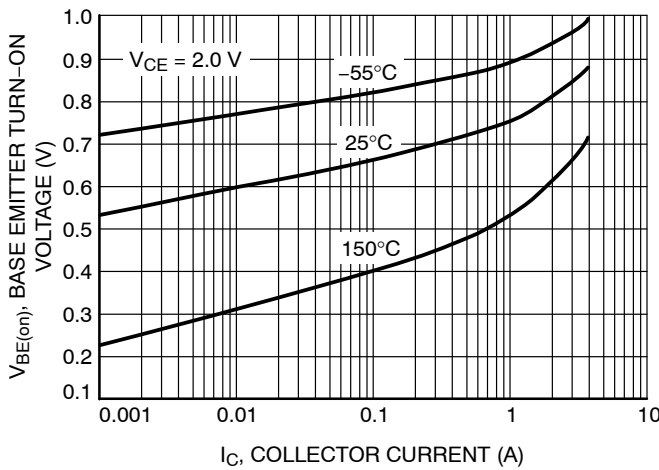Figure 4. Base Emitter Saturation Voltage vs. Collector Current

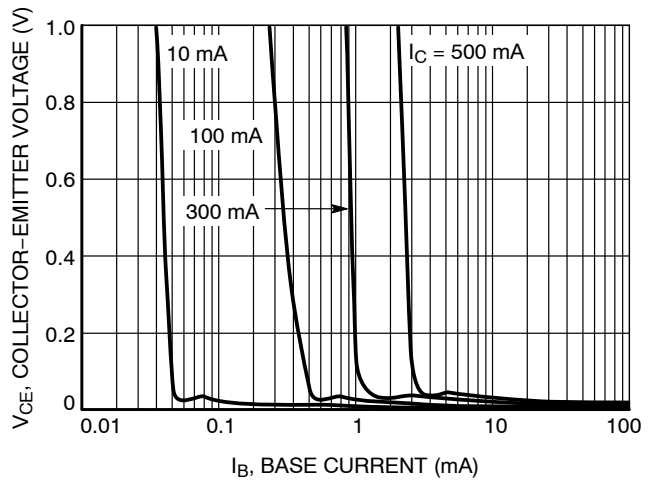Figure 5. Base Emitter Turn–On Voltage vs. Collector Current
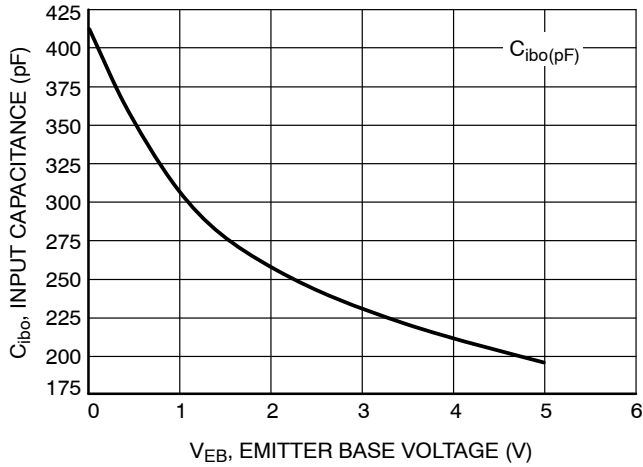

Figure 6. Saturation Region

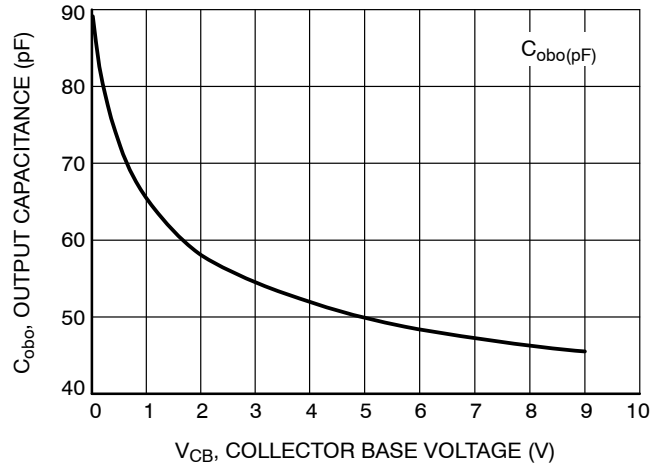## TYPICAL CHARACTERISTICS

Figure 7. Input Capacitance

Figure 8. Output Capacitance
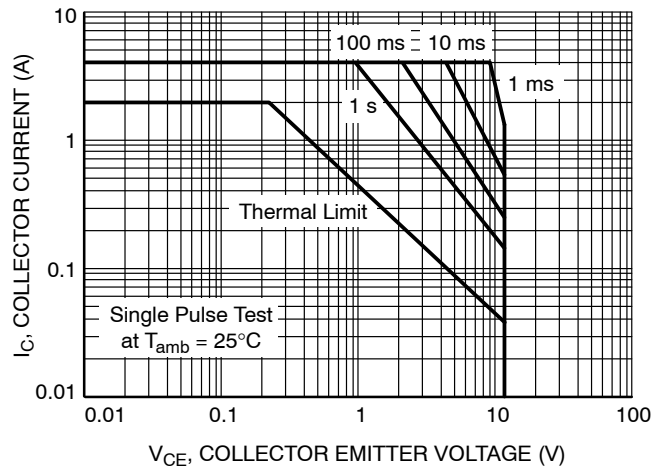
Figure 9. Safe Operating Area

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

SOT−23 (TO−236)
CASE 318−08
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

TOP VIEW

VIEW C

SIDE VIEW

END VIEW

SEE VIEW C

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	–––	10°	0°	–––	10°

RECOMMENDED SOLDERING FOOTPRINT

2.90

3X 0.90

3X 0.80

0.95
PITCH

DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*

XXXM■
.
1

XXX = Specific Device Code
M = Date Code
■ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot " ■ ", may or may not be present.

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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PUBLICATION ORDERING INFORMATION

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